# SLG7NT4445 GreenPAK 2<sup>™</sup>



## **Reset IC with Latch and MUX**

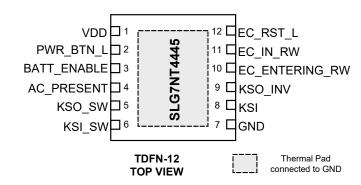
#### **General Description**

Renesas GreenPAK 2 SLG7NT4445 is a low power and small form device. The SoC is housed in a 2.5mm x 2.5mm TDFN package which is optimal for using with small devices.

#### **Features**

- Low Power Consumption
- Dynamic Voltage Supply Range
- RoHS Compliant / Halogen-Free
- Pb-Free TDFN-12 Package
- MSL1

#### **Pin Configuration**

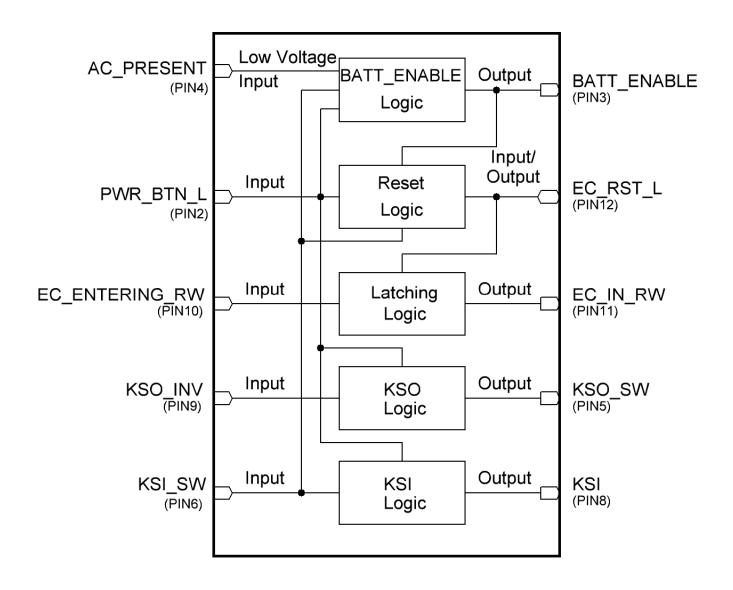


#### **Output Summary**

- 1 Output Push Pull 1X
- 4 Outputs Open Drain NMOS 1X



## **Block Diagram**





# **Pin Configuration**

Pin#	Pin Name	Туре	Pin Description
1	VDD	PWR	Supply Voltage
2	PWR_BTN_L	Digital Input	Digital Input with Schmitt trigger
3	BATT_ENABLE	Digital Output	Open Drain NMOS 1X
4	AC_PRESENT	Digital Input	Low Voltage Digital Input
5	KSO_SW	Digital Output	Open Drain NMOS 1X
6	KSI_SW	Digital Input	Digital Input with Schmitt trigger
7	GND	GND	Ground
8	KSI	Digital Output	Open Drain NMOS 1X
9	KSO_INV	Digital Input	Digital Input with Schmitt trigger
10	EC_ENTERING_RW	Digital Input	Digital Input with Schmitt trigger
11	EC_IN_RW	Digital Output	Open Drain NMOS 1X
12			Digital Input withSchmitt trigger / Push Pull 1X
Exposed Bottom Pad	Exposed Bottom Pad	GND	Ground

**Ordering Information** 

<u> </u>	-
Part Number	Package Type
SLG7NT4445V	V = TDFN-12
SLG7NT4445VTR	VTR = TDFN-12 - Tape and Reel (3k units)



### **Absolute Maximum Conditions**

Parameter	Min.	Max.	Unit
V <sub>HIGH</sub> to GND	-0.3	7	٧
Voltage at input pins	-0.3	7	V
Current at input pin	-1.0	1.0	mA
Storage temperature range	-65	150	°C
Junction temperature		150	°C

#### **Electrical Characteristics**

(@ 25°C, unless otherwise stated)

Symbol	Parameter	Condition/Note	Min.	Тур.	Max.	Unit	
$V_{DD}$	Supply Voltage		1.71		5.5	V	
TA	Operating Temperature		-40	25	85	°C	
lα	Quiescent Current	Static inputs and outputs		1		μA	
I <sub>A</sub>	Active Current	Static inputs and outputs		15		μΑ	
Vo	Maximal Voltage Applied to any PIN in High-Impedance State				VDD	<b>V</b>	
lo	Maximal Average or DC Current (note 1)	Per Each Chip Side			24	mA	
		Logic Input with Schmitt Trigger, at VDD=1.8V	1.35		VDD		
	HIGH-Level Low Voltage Input Voltage	Low-Level Logic Input, at VDD=1.8V	1.1		VDD		
ViH		Logic Input with Schmitt Trigger, at VDD=3.3V	2.3		VDD	V	
		Low-Level Logic Input, at VDD=3.3V	1.5		VDD		
		Logic Input with Schmitt Trigger, at VDD=5.0V	3.2		VDD		
		Low-Level Logic Input, at VDD=5.0V	1.7		VDD		
		Logic Input with Schmitt Trigger, at VDD=1.8V			0.45		
		Low-Level Logic Input, at VDD=1.8V			0.50		
VIL	LOW-Level Low Voltage Input Voltage	Logic Input with Schmitt Trigger, at VDD=3.3V			0.92	V	
		Low-Level Logic Input, at VDD=3.3V			0.66		
		Logic Input with Schmitt Trigger, at VDD=5.0V		1.3			



		Low-Level Logic Input, at VDD=5.0V		 0.77	
Іін	HIGH-Level Input Current	Logic Input Pins;V <sub>IN</sub> = VDD	-1.0	 1.0	μA
I <sub>IL</sub>	LOW-Level Input Current	Logic Input Pins; V <sub>IN</sub> = 0V	-1.0	 1.0	μA
		Push Pull, I <sub>OH</sub> = 100uA, 1X Driver, at VDD=1.8 V	1.66	 	
		Push Pull, I <sub>OH</sub> = 700uA, 1X Driver, at VDD=1.8 V	1.21	 	
Vон	HIGH-Level Output Voltage (note 1)	Push Pull, I <sub>OH</sub> = 3mA, 1X Driver, at VDD=3.3 V	2.1	 	V
		Push Pull, I <sub>OH</sub> = 5mA, 1X Driver, at VDD=5.0 V	3.6	 	
		Push Pull, I <sub>OH</sub> = 8mA, 1X Driver, at VDD=5.0 V	2.9	 	
		Push Pull, I <sub>OL</sub> = 100uA, 1X Driver, at VDD=1.8 V		 0.040	
		Push Pull, I <sub>OL</sub> = 700uA, 1X Driver, at VDD=1.8 V		 0.415	
	LOW-Level Output Voltage (note 1)	Open Drain, I <sub>OL</sub> = 5mA, 1X Driver, at VDD=1.8 V		 0.340	
		Push Pull, I <sub>OL</sub> = 3mA, 1X Driver, at VDD=3.3 V		 0.81	
VoL		Open Drain, I <sub>OL</sub> = 20mA, 1X Driver, at VDD=3.3 V		 0.605	V
		Push Pull, I <sub>OL</sub> = 5mA, 1X Driver, at VDD=5.0 V		 0.85	
		Push Pull, I <sub>OL</sub> = 8mA, 1X Driver, at VDD=5.0 V		 1.2	
		Open Drain, I <sub>OL</sub> = 20mA, 1X Driver, at VDD=5.0 V		 0.36	
		Push Pull, V <sub>OL</sub> =0.15V, 1X Driver, at VDD=1.8 V	0.34	 	
		Open Drain, V <sub>OL</sub> =0.15V, 1X Driver, at VDD=1.8 V	2.72	 	
Іоь	LOW-Level Output Current (note 1)	Push Pull, V <sub>OL</sub> =0.4V, 1X Driver, at VDD=3.3 V	1.836	 	mA
		Open Drain, V <sub>OL</sub> =0.4V, 1X Driver, at VDD=3.3 V	14.688	 	
		Push Pull, V <sub>OL</sub> =0.4V, 1X Driver, at VDD=5.0 V	2.745	 	

# **SLG7NT4445**



# **Reset IC with Latch and MUX**

		Open Drain, V <sub>OL</sub> =0.4V, 1X Driver, at VDD=5.0 V	21.96				
R <sub>PULL_UP</sub>	Internal Pull Up Resistance	Pull up on PINs 6, 12	35	50	65	kΩ	
D	R <sub>PULL_DOWN</sub> Internal Pull Down Resistance	Pull down on PIN10		35	50	65	kΩ
RPULL_DOWN		Pull down on PIN9	210	300	390	K77	
T <sub>DLY0</sub>	Delay0 Time	At temperature 25°C	4.13	5	5.88	ms	
T <sub>DLY1</sub>	Delay1 Time	At temperature 25°C	8.27	10	11.7	ms	
T <sub>DLY2</sub>	Delay2 Time	At temperature 25°C	5		7.042	s	
T <sub>DLY3</sub>	Delay3 Time	At temperature 25°C	60		127	μs	
Tsu	Start up Time	After VDD reaches 1.6V level		7		ms	

<sup>1.</sup> Guaranteed by Design.



#### **Description**

This device is a reset IC with one shot function, internal Latching system, level shifter and multiplexor. The reset (active LOW) occurs when both PWR\_BTN\_L (PIN2) and KSI\_SW (PIN6) are LOW. PWR\_BTN\_L (PIN2) has 5ms deglitch delay on its line. Also reset logics contains one more 100µs deglitch delay is used. The signal from this delay goes to 10ms one-shot system that creates 10ms LOW pulse on reset event. If PWR\_BTN\_L and KSI\_SW are LOW, and AC\_PRESENT (PIN4) transitions from HUGH to LOW, these three conditions will latch the BATT\_ENABLE (PIN3) LOW for 5 seconds minimum. During this EC\_RST\_L will be asserted and EC\_IN\_RW will go LOW as well.

EC\_RST\_L is configured to be bidirectional, so it will operate as digital input with Schmitt trigger or as Low Level Digital Output.

Also SLG7NT4445 includes latching system. Its inputs are EC\_RST\_L and EC\_ENTERING\_RW. EC\_IN\_RW is an output configured as open drain. This system is initialized with logic HIGH on its output. It is latched LOW when EC\_RST\_L goes LOW until EC\_ENTERING\_RW goes HIGH.

Multiplexing system in this device follow the logic:

KSO SW = PWR BTN L && !KSO INV

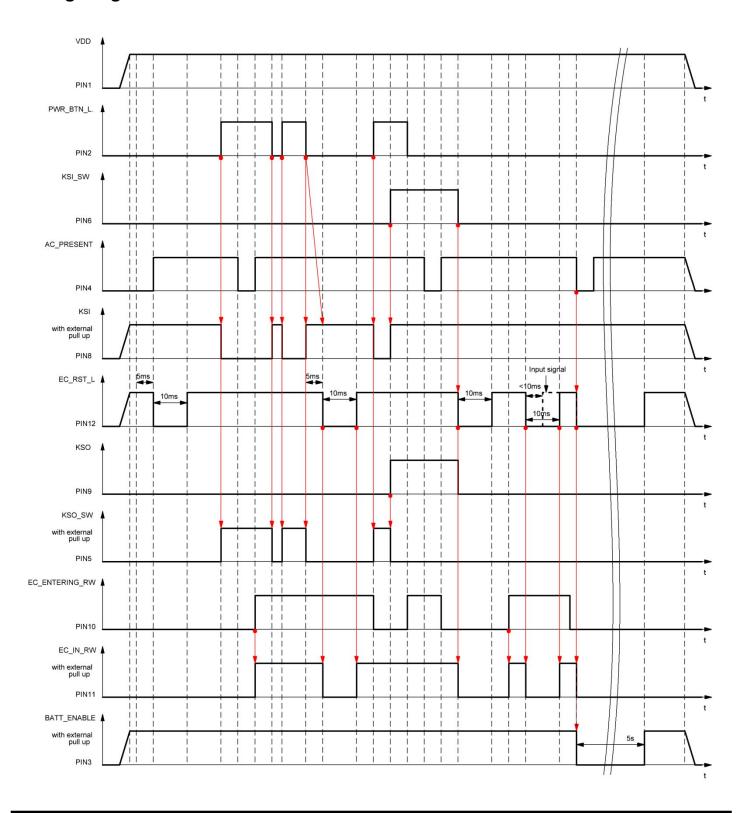
KSI = !(PWR\_BTN\_L) | KSI\_SW

If the AC\_PRESENT / BATTERY\_ENABLE functionality is not needed, BATTERY\_ENABLE can be left floating but AC\_PRESENT should be tied low.

All pins are in a high impedance state until the chip has powered up.

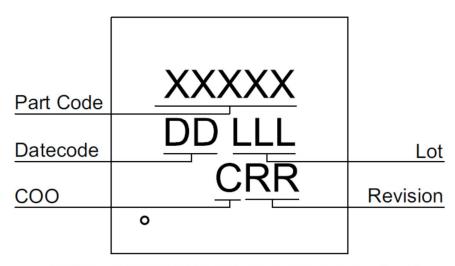


## **Timing Diagram**





## **Package Top Marking**



XXXXX - Part ID Field: identifies the specific device configuration

DD - Date Code Field: Coded date of manufacture

LLL – Lot Code: Designates Lot #
 C – COO: Specifies Country of Origin
 RR – Revision Code: Device Revision

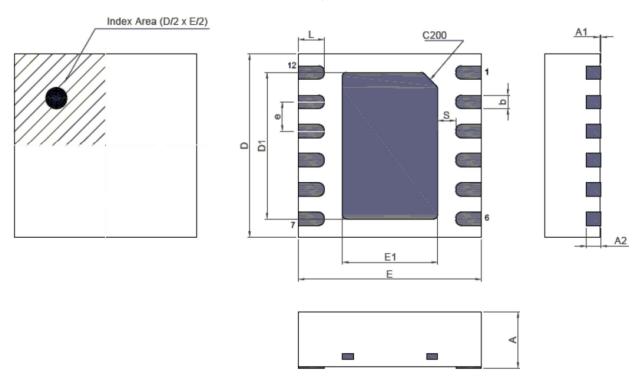
Datasheet Revision	Programming Code Number	Locked Status	Part Code	Revision	Date
1.03	002	Ш	4445V	AB	02/25/2022

The IC security bit is locked/set for code security for production unless otherwise specified. Revision number is not changed for bit locking.



## **Package Drawing and Dimensions**

### 12 Lead TDFN Package JEDEC MO-252, Variation 2525E



#### Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
Α	0.70	0.75	0.80	D1	1.95	2.00	2.05
A1	0.005	-	0.060	E1	1.25	1.30	1.35
A2	0.15	0.20	0.25	е	0.40 BSC		
b	0.13	0.18	0.23	L	0.30	0.35	0.40
D	2.45	2.50	2.55	S	0.18 -		-
E	2.45	2.50	2.55				



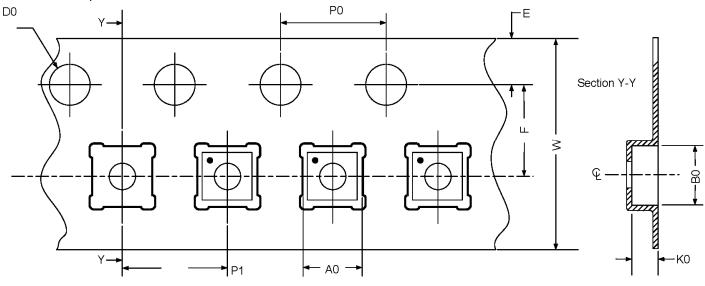
**Tape and Reel Specification** 

Package Type	# of	Dackado	Max Units		Reel &	Trailer A		Leader B		Pocket (mm)	
	Pins		per reel	per box	Hub Size (mm)	Pockets	Length (mm)	Pockets	Length (mm)	Width	Pitch
TDFN 12L 2.5x2.5mm 0.4P Green	12	2.5x2.5x0.75	3000	3000	178/60	42	168	42	168	8	4

## **Carrier Tape Drawing and Dimensions**

Package Type	Pocket BTM Length (mm)	Pocket BTM Width (mm)	Pocket Depth (mm)	Index Hole Pitch (mm)	Pocket Pitch (mm)	Index Hole Diameter (mm)	Index Hole to Tape Edge (mm)	Index Hole to Pocket Center (mm)	Tape Width (mm)
	Α0	В0	K0	P0	P1	D0	E	F	w
TDFN 12L 2.5x2.5mm 0.4P Green	2.75	2.75	1.05	4	4	1.55	1.75	3.5	8

Refer to EIA-481 Specifications



## **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 4.6875 mm³ (nominal). More information can be found at <a href="https://www.jedec.org">www.jedec.org</a>.

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